ABSTRACT OF THE DISCLOSURE

A semiconductor laser device includes a QW active layer structure including a Ga_xIn_1 $_xAs_{1.y}Sb_y$ layer wherein $0.3 \le 1$ -x and $0.003 \le y \le 0.008$, or a QW active layer structure including a $Ga_xIn_{1-x}A_{s_1-y_1-y_2}N_{y_1}Sb_{y_2}$ layer wherein $0.3 \le 1$ -x, 0 < y1 < 0.03 and $0.002 \le y2 \le 0.06$. The semiconductor laser device suppresses the three-dimensional epitaxial growth, and has superior optical characteristics including a low threshold current.

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